

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	1010	(via or metallization) same (("silicon nitride" or SiN or "Si.sub.3N.sub.4") and ("silicon carbide" or SiC))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 17:50			0
2	BRS	L2	324	1 and @pd<=20011127	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 16:45			0
3	BRS	L3	317	1 and @pd<=20011106	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 17:53			0
4	BRS	L4	153	etch\$ same (trench or opening or via) same ((deposit\$3 or form\$3) with (metal or metallizaiton)) same (("silicon nitride" or SiN or "Si.sub.3N.sub.4") and ("silicon carbide" or SiC))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 18:07			0
5	BRS	L5	21	4 and @pd<=20011106	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 17:53			0
6	BRS	L6	0	5 not 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 18:07			0
7	BRS	L7	132	4 not 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 18:07			0